

TM18P03S

P-Channel Enhancement Mosfet

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30	-	-	V	
Gate-body Leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V	T _J =25°C	-	-	-1	μA
			T _J =100°C	-	-	-100	
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.8	2.5	V	
Drain-Source On-Resistance ⁴	R _{DS(on)}	V _{GS} = -10V, I _D = -12A	-	8.8	12	mΩ	
		V _{GS} = -4.5V, I _D = -10A	-	13	15		
Forward Transconductance ⁴	g _{fs}	V _{DS} = -10V, I _D = -10A	-	50	-	S	
Dynamic Characteristics⁵							
Input Capacitance	C _{iss}	V _{DS} = -15V, V _{GS} = 0V, f = 1MHz	-	2100	-	pF	
Output Capacitance	C _{oss}		-	430	-		
Reverse Transfer Capacitance	C _{rss}		-	358	-		
Gate Resistance	R _g	f=1MHz	-	9.5	-	Ω	
Switching Characteristics⁵							
Total Gate Charge	Q _g	V _{GS} = -10V, V _{DS} = -15V I _D = -12A	-	35	-	nC	
Gate-Source Charge	Q _{gs}		-	9.9	-		
Gate-Drain Charge	Q _{gd}		-	10.5	-		
Turn-On Delay Time	t _{d(on)}	V _{GS} = -10V, V _{DD} = -15V R _G = 3Ω, I _D = -12A	-	10.8	-	ns	
Rise Time	t _r		-	13.2	-		
Turn-Off Delay Time	t _{d(off)}		-	73	-		
Fall Time	t _f		-	35	-		
Reverse Recovery Time	t _{rr}	I _F = -12A, dI _F /dt = 100A/μs	-	25	-	ns	
Reverse Recovery Charge	Q _{rr}		-	10	-	nC	
Drain-source body diode Characteristics							
Diode Forward Voltage ⁴	V _{SD}	I _S = -1A, V _{GS} = 0V	-	-	-1.2	V	
Continuous Source Current	I _S	T _A =25°C	-	-	-18	A	

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.
2. The EAS data shows Max. rating . The test condition is V_{DD}= -25V, V_{GS}= -10V, L=0.1mH, I_{AS}= -40A.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.



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Typical Characteristics

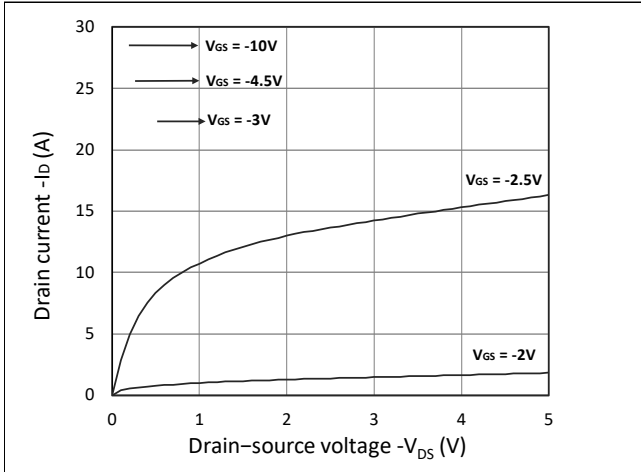


Figure 1. Output Characteristics

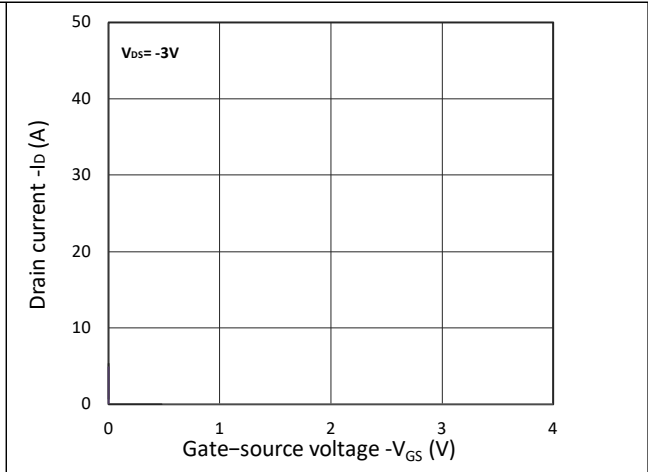


Figure 2. Transfer Characteristics

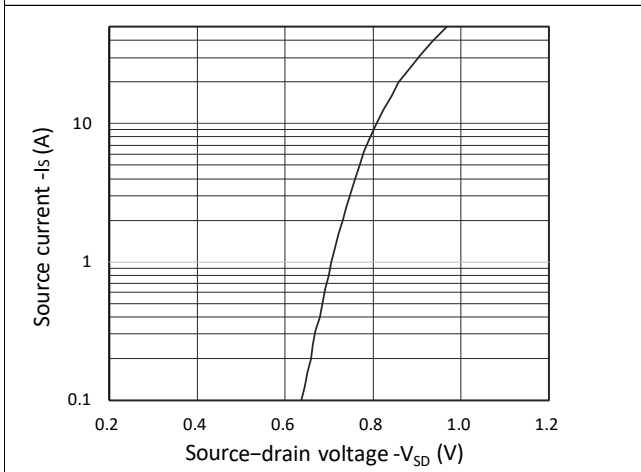


Figure 3. Forward Characteristics of Reverse

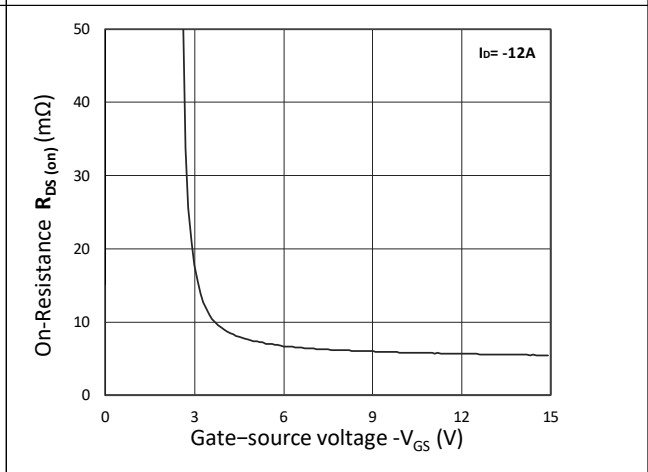


Figure 4. $R_{DS(on)}$ vs. V_{GS}

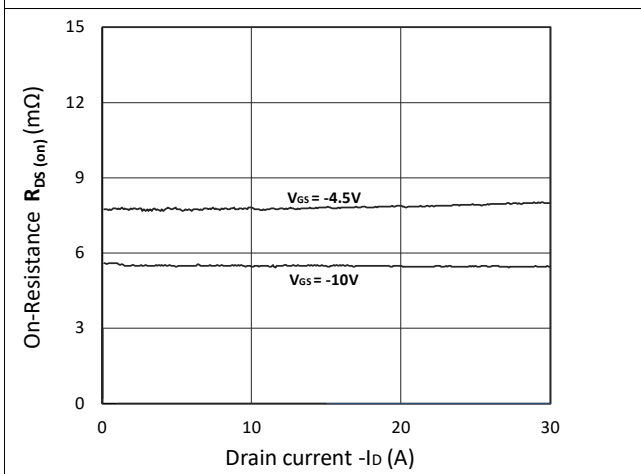


Figure 5. $R_{DS(on)}$ vs. I_D

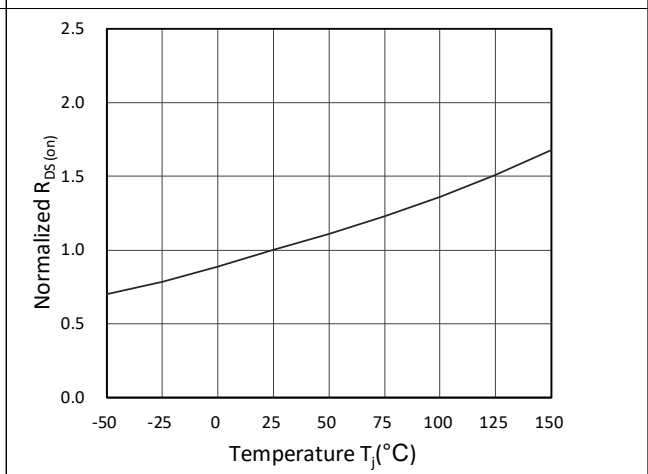


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

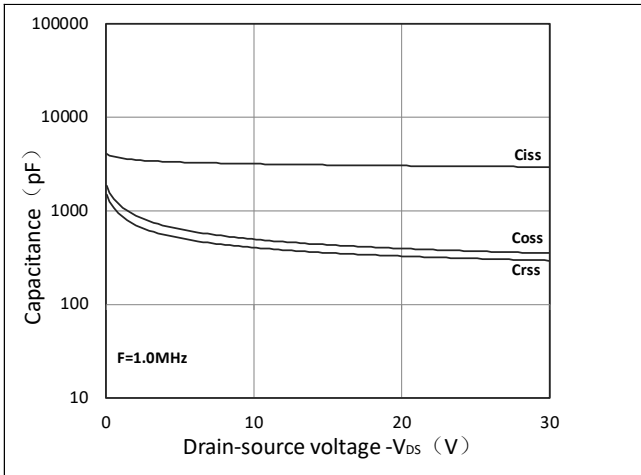


Figure 7. Capacitance Characteristics

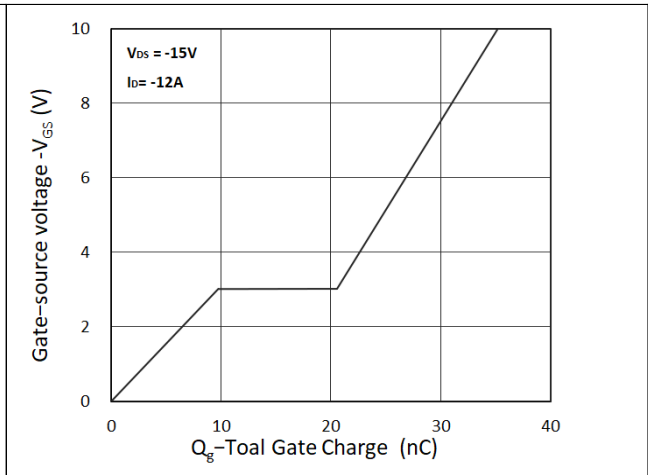


Figure 8. Gate Charge Characteristics

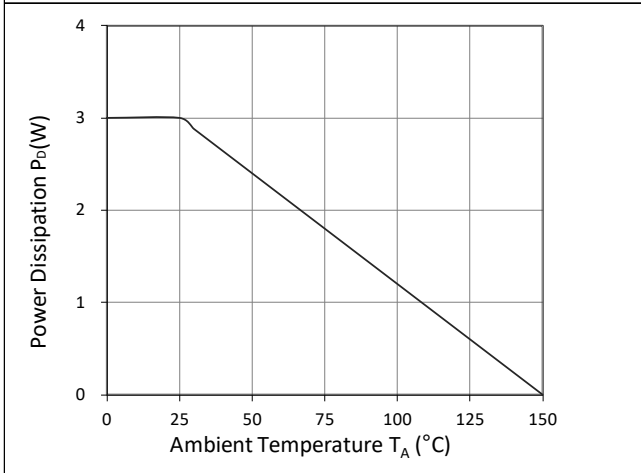


Figure 9. Power Dissipation

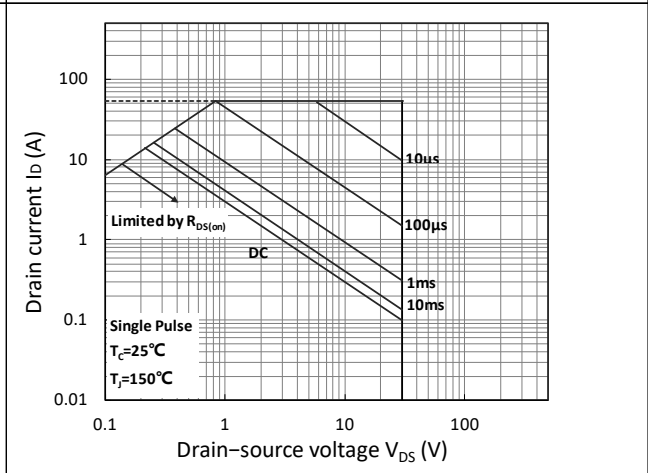


Figure 10. Safe Operating Area

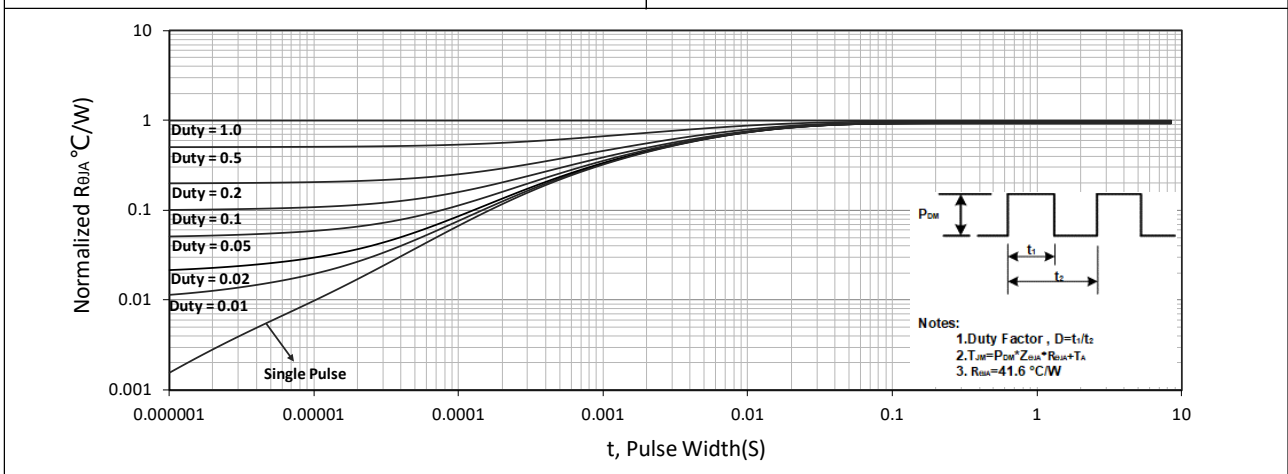


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

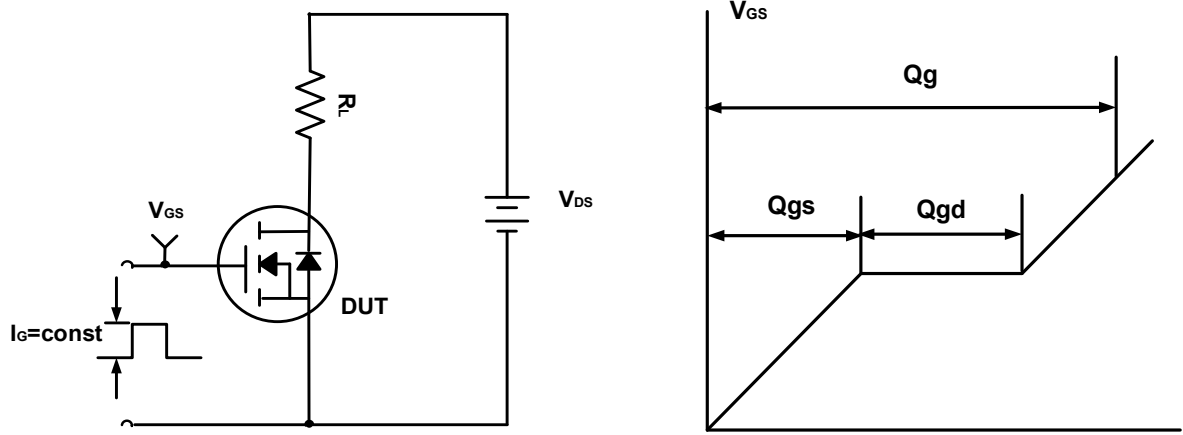


Figure A. Gate Charge Test Circuit & Waveforms

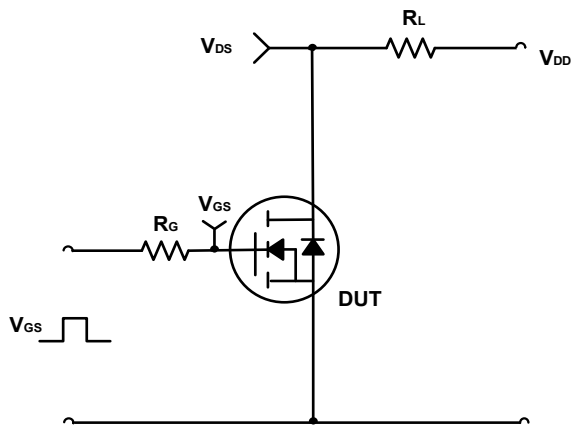


Figure B. Switching Test Circuit & Waveforms

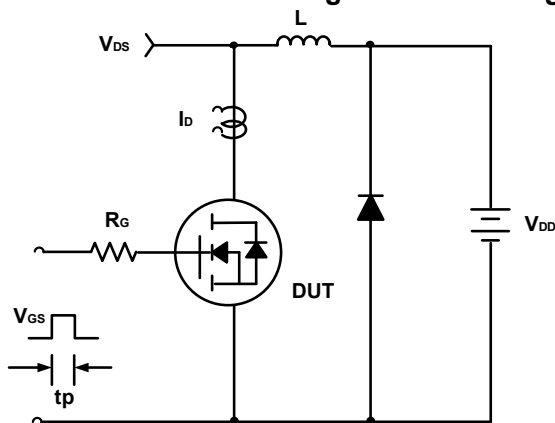
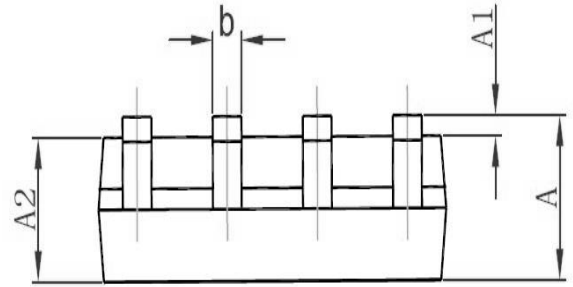
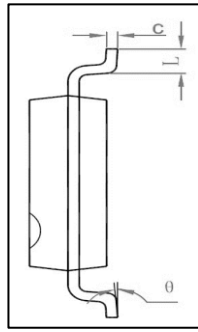
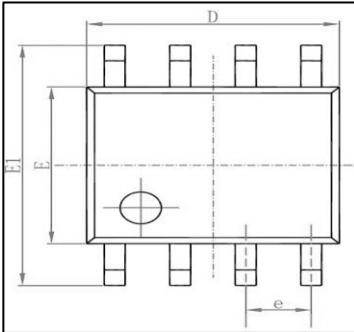
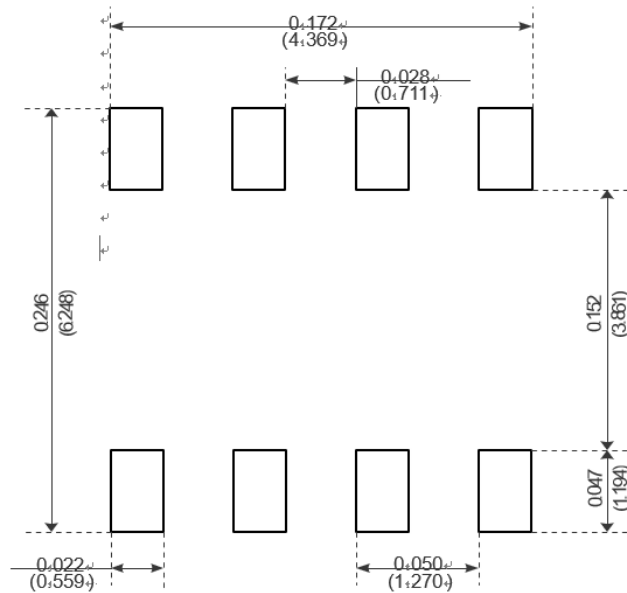


Figure C. Unclamped Inductive Switching Circuit & Waveforms

Package Mechanical Data:SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads